Current R ecti cation by M olecules with A sym m etric Tunneling B arriers

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A simple experimentally accessible realization of current rectication by molecules (molecular lms) bridging metal electrodes is described. It is based on the spatial asymmetry of the molecule and requires only one resonant conducting molecular level (orbital). The rectication, which is due to asymmetric coupling of the level to the electrodes by tunnel barriers, is largely independent of the work function difference between the two electrodes. Results of extensive numerical studies of the family of suggested molecular recti ers $HS-(CH_2)_m - C_6H_4 - (CH_2)_n - SH$ are presented. The highest rectication ratio 500 is achieved at m = 2 and n = 10.

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I. IN TRODUCTION

The concept of a molecular recti er started the eld of m olecular electronics (moletronics) almost thirty years ago [1]. At present, moletronics is an explosively growing eld of experimental and theoretical activity. The molecular recti er (MR) is still one of the central objects of this research. Even the simplest future application, such as molecular memory, will require high quality MR with sharp voltage thresholds, large current recti cation ratios, sm all time constants, large breakdown voltages and so on. MR demonstrated so far [2{4] constitute an impressive proof of principle but their electrical parameters are in fact very poor. The situation prompts further investigation of molecular recti cation.

Until recently, theoretical analysis of MR had been largely limited to the Aviram and Ratner donor-A) mechanism [1]. In this insulator-acceptor (D design, the highest occupied m olecular orbital (HOMO) and the low est unoccupied m olecular orbital (LUM 0) are con ned to two di erent parts of the recti er, D and A respectively. The insulating bridge prevents the orbitals from \spilling o " to the other part. If such a m olecule is placed between twom etalelectrodes, the current-voltage characteristics of the junction is expected to be highly asymmetric. At a particular voltage applied in the positive direction, the Ferm i level of the electrode on A side aligns with the LUMO, and the on D side aligns with the HOMO. At this voltage, the current rises sharply because the electrons can now be loaded on the LUMO, then tunnel inelastically through the to the HOMO and the escape into the second electrode. In the opposite direction, a sim ilar process does not occur until a much higher applied voltage.

A di erent m echanism of m olecular recti cation was described by E llenbogen and Love [5]. It is based on an energy m ism atch between two conducting levels localized on di erent parts of the m olecule. W ithin the D A fram ework, such levels could, for instance, be the LU-

M O s of D and A. Under external bias, the levels shift because of the electric eld. In the forward direction, the conducting levels align at some voltage, and facilitate resonant transport of electrons between the electrodes. In the reverse direction, the levels move away from each other and the current remains small. Hence molecular recti cation.

W e note that both described m echanism s require two electroactive m olecular levels and a ne balance between potential drops inside the m olecule and on the m oleculeelectrode interfaces. To the best of our know ledge, neither of the m echanism has been realized experim entally.

Recently, an interesting case of molecular recti cation was discussed by Krzeminski et al. [6]. They studied theoretically current recti cation in Langmuir-Blodgett (LB) In s of -hexadecylquinolinium tricyanoquinodim ethanide (C16H33Q-3CNQ), which was previously studied experimentally [2,3]. That molecule was initially considered to be a possible in plementation of the A viram -R atnerm echanism because its active part $\ensuremath{\texttt{Q}}\xspace{-3C}\ensuremath{\,\text{N}}\xspace{\,\texttt{Q}}\xspace{\,\text{C}}\xspace{\,\text{N}}\xspace{\,\text{C}}\xspace{\,$ insulating tail C₁₆H₃₃ was added to help form good LB lm s.) It was later realized [7] that the Q-3CNQ is, in A molecule and is unlikely to implement fact, a D the Aviram -Ratner mechanism. The analysis of Ref. [6] con med that the bridge does not su ciently isolate D and A to keep molecular orbitals localized on either D or A. Instead, the orbitals were delocalized over the entire Q-3CNQ unit. K rzem inski et al. have attributed the observed recti cation to asymmetric position of the LUMO and HOMO with respect to the Ferm i levels of the metal and to \asymmetric pro le of electrostatic potential across the system ".

The purpose of this paper is to point out that there is, indeed, a simple and general mechanism of molecular recti cation where a single electroactive unit is positioned asymmetrically with respect to electrodes and the HOMO and LUMO are positioned asymmetrically with respect to the Ferm i level. However, this mechanism does not require such com plex molecules as $C_{16}H_{33}Q$ -3CNQ. W hat is needed is just one conducting molecular level placed closer to one electrode than to the other. Since most of the applied voltage drops on the longer insulating barrier, the conditions for resonant tunneling through the level are achieved at very di erent voltages for the two opposite polarities. By changing the lengths of the insulating barriers, the recti cation ratio can be system atically changed. This mechanism can be realized by relatively simple molecules. For instance, the conductive level could be supplied by a benzene ring. A lso, the m olecules can be shorter, produced by e.g. self-assem bly instead of LB deposition, and therefore m ore conductive. Indeed, the currents reported in $[\beta]$ were of order 10 17 A/m olecule, which alm ost rules out any practical application of such MR. This is obviously a result of having the long aliphatic tail $C_{16}H_{33}$. There is an experim ental evidence that even much shorter alkane chains, like C_{12} , are very resistive and transport there proceeds by hopping processes rather than tunneling [8]. We show below that W ith simpler conducting and shorter insulating units, M R can achieve recti cation ratios in excess of a hundred while remaining fairly conductive.

In the foregoing sections, we discuss the present mechanism of molecular recti cation in more detail. We have performed a numerical analysis of the mechanism by calculating the current-voltage (I-V) characteristics of the family of prototype molecular diodes HS -(CH₂)_m -C₆H₄-(CH₂)_n -SH. We have found that recti cation ratios of > 100 are achievable with such a design.

We mention for completeness that any asymmetric electrode-molecule-electrode junction should in principle produce asymmetric currents at large enough voltages. Such a high-voltage asymmetry due to unequal coupling to the electrodes [9,10] or to an asymmetric central molecular unit [11] have been observed experimentally and discussed theoretically. However, the current rectication ratios in these studies were of order unity, which is clearly insu cient for practical applications. Zhou et al reported rectication in a molecular monolayer of 4thioacetylbiphenyl [4]. In that experiment, the two electrodes were dierent, with dierent work functions, and dierent connections to the molecules. The experimental data were interpreted as the standard therm ionic em ission through an asymmetric barrier.

II.A MOLECULAR DESIGN FOR CURRENT RECTIFICATION

Our molecular recti ers with asymmetric tunneling barriers consist of ve structural parts, see Fig. 1. The end groups provide contact to the two electrodes. For instance, these m ay be thick that could self-assem ble on the surface of gold or silver, carboxyl groups in case the Langmuir-B lodgett technique is used, and so on. The end



FIG.1. Top: Schem atic structure of an asym m etric tunneling barrier m olecular recti er. Bottom : The (2,6) m em ber of the M R fam ily $HS-(CH_2)_m - C_{6H_4}-(CH_2)_n - SH$.

FIG.2. The basic principle of recti cation by asymmetric tunnel barriers. W is the work function of the metal, A is the electron a nity of them olecule, W A. (b) A molecule with A W and with dierent lengths of the insulating barriers is connected to two metallic leads. (c) Under forward bias, the current rises when the right Fermi level aligns with the conducting molecular level. (d) Under reverse bias, the current rises when the left Fermi level aligns with the conducting molecular level. Since most of the total voltage drops on the right insulation barrier, $V_R > V_F$. See the attached * gif le.

groups m ay even be absent altogether if the application does not require them to provide better contacts. The three inner parts of MR are the central conjugated group C and two insulating barriers I_L and I_R . The purpose of such a construction is to provide an electronic level localized on C, with energy not very di erent from the Ferm i energies of the electrodes. In most cases this level will be the lowest unoccupied molecular orbital (LUMO) of them olecule. Then the electron transm ission probability should be resonant near the energy of the LUMO.

The energy diagram of MR is shown in Fig.2. The two main parameters that determ ine the rectication properties of MR are the energy dierence between the LUMO and the Fermi energy of the electrodes = W A, and the ratio of the voltage drops on the right and left insulating parts . Under the assumption that the polarizability of C is much larger than that of the Is, the voltage drops on the barriers are proportional to their respective lengths L_{right} and L_{left} , and $I_{right}=L_{left}$. For simplicity, we assume that the two electrodes are similar, or have similar work functions. Therefore there is no contact potential dierence and the electric eld on the molecule is

zero at zero applied bias. The m inor com plications that may arise from the contact potential di erence will be brie y discussed in Section V. Let us consider the operating principle of MR.We shall follow the convention that the right electrode is always grounded and the right Ferm i energy can be used as the reference energy. Then a positive potential applied to the left electrode shifts its electronic levels to lower absolute energies. Thus under positive bias, the Ferm i energy of the left electrode goes down.Due to the non-zero electric eld, the LUMO will be dragged down too. The energy shift of the LUM O ${\rm 4~E_{~LUM~O}}$ is determ ined by the parameter $% 100\,{\rm MeV}$. Under our assumptions, the eld across C is very small, and the potential drops on the two barriers, U left and U right have to sum up to the total external bias V, $U_{left} + U_{right} = V$. Then it is easy to show that

$$4 E_{LUMO} = U_{right} = \frac{1}{1+q} V; \qquad (1)$$

where q is the elementary charge. A sharp increase in current is expected when the LUMO lines up with the right Ferm i level, that is at $4 E_{LUMO} = .$ The corresponding forward voltage follows from Eq. (1)

$$V_{\rm F} = \frac{1+}{q}$$
: (2)

Under reverse bias, both the left Ferm i level and the LUMO go up in energy. The current will turn on when the left Ferm i level lines up with the LUMO, when $= U_{left} = V = U_{right}$. This corresponds to a reverse voltage

$$V_{\rm R} = (1 +) - \frac{1}{q}$$
: (3)

C learly, the forward and reverse voltages are di erent, their ratio being $V_{\rm R}$ =V_F = . At a large , the two thresholds di er, and there is a voltage window $V_{\rm F}$ < $jV~j<~V_{\rm R}$ within which there is a substantial current in the forward direction and alm ost no current in the reverse direction. Hence, a strong rectifying e ect is expected.

D i erent parts of M R a ect di erent properties of the I-V characteristic. Parameter determ ines the overall scale of the forward and reverse voltages. itself could be system atically changed by using di erent materials for the electrodes and di erent conductive parts C. The work functions of the electrodes used in moletronics studies vary from 5.6 eV (Pt) to 4.0 eV (Si), enabling alm ost continuous adjustment of . (O bviously, any changes of the electrode material have to be compensated by respective changes of the side groups of M R.) The use of di erent materials for the two electrodes provides further tuning of . Indeed, the contact potential changes energy of the LUM O by some additional amount. [Cf. Eq. (1) and use the contact potential in place of bias V.] The conclusion from this qualitative analysis is that is

a param eter under the control of a designer of m olecular recti ers. W hat absolute value of , large or small, is optim al from the electronic view point is not clear a priori. Increasing widens the recti cation window and im proves the stability of the device. At the same time, larger s im ply higher operating voltages, power dissipation and other unwelcom e consequences.

The shortest of the two insulating barriers controls the width of the conducting leveland consequently the sharpness of the current increase in the vicinity of $V_{\rm F}\,$ and $V_{\rm R}$. Indeed, the transm ission probability T (E) through a molecular level, which de nes the conductance of the molecule G (E) / T (E) according to standard Landauer form alism [14], is well described by the Breit-W igner form ula

$$T (E) = \frac{L R}{(E E_{MO})^2 + \frac{1}{4} (L + R)^2}; \quad (4)$$

where E_{MO} is the energy of the molecular orbital available for resonant transmission (LUMO in the present case), and L_{R} are the partial widths associated with coupling to the left and right electrodes, respectively, see analysis in [18]. The \golden rule" estimate gives $t_{L,R}^2 = D_{L,R}$, $t_{L,R}$ being the elective coupling ma-L;R trix element and D $_{\rm L\,;R}$ the electron bandwidth in the electrodes. We see that a steep rise in current occurs when one of the electrode Ferm i levels rises to line up with E_{MO} , which is exactly what is required for large recti – cation ratios. If the C component of the molecule is too close to a m etal, the conducting level is so broad that the transm ission probability will be substantial at all energies. Indeed, $_{\rm i}$ / e $^{2 \ L_{\rm i}}$; where / (E $_{\rm barrier}$ E $_{\rm F}$) $^{1=2}$ is the tunneling attenuation coe cient. Here E barrier is the energy of of the conducting level of the insulating barrier, which lies higher that the LUM 0 of the conducting unit C. For alkane chains on gold, (E barrier E_F) 4:8 eV [8]. Thus the width of the level is exponentially sensitive to the distance from the electrode. If the level is substantially broadened, there will be little di erence between the currents in the forward and reverse directions. Su cient insulation of the conducting molecular orbital from both electrodes is an essential feature of the present recti cation m echanism .

Finally, the longest of the two barriers controls the anisotropy of the I-V characteristic and the overall am – plitude of the current. A s was discussed above, $V_R = V_F$ L_{right}=L_{left}. Therefore the longer the second barrier the larger the $V_R = V_F$ ratio and the better the diode. At the same time, the current goes down exponentially with the barrier length. Indeed, the current is

$$I = \frac{2q}{h}^{Z} dE f E \frac{qV}{2} f E + \frac{qV}{2} T (E)$$
$$= \frac{2q}{h} \frac{L R}{L + R} \frac{2q}{h} R / e^{2 L};$$
(5)

FIG.3. A monolayer of molecular diodes between two sem i-in nite fcc electrodes. Only one layer of electrode atom s is shown. The solid line encloses the atom s included in one molecular complex. See the attached * gif le.

when the resonance falls into the $\$ indow" between the lowest and the highest Ferm i levels in the leads. The current falls o exponentially with the thickness of the thicker of the insulating barriers $L_>$. Therefore, we are facing a typical trade-o problem but in its worst form. The asymmetry of M R in proves linearly but the resistance grows exponentially with the length of the barrier. N onetheless, we found that substantial recti cation is achieved at the current levels that make electronic applications of M R practical. This is detailed in the next sections.

III. CALCULATION DETAILS

In order to test the proposed mechanism of molecular recti cation, we calculated the I-V characteristics of a prototype family of molecular diodes $HS-(CH_2)_n-C_6H_4-(CH_2)_m$ -SH sandwiched between two gold electrodes. The ve functional parts of MR are constructed from the standard chemical groups used in moletronic studies. The end thick -SH chemically attach the molecules to gold, the middle benzene ring provides a conducting level (LUMO) at energy $E_{LUMO} = 3.5 \text{ eV}$ (with respect to vacuum), and the insulating barriers are made of saturated hydrocarbon units -CH₂-. Individualmem bers of the family are parameterized by the two integers (n;m) which are the respective num bers of the -CH₂-groups on both sides of the molecules.

The electrode-MR-electrode junction is shown in Fig. 3. The equilibrium structure of isolated molecules was obtained through total energy m in im ization with the density-functional program Spartan [13]. An important factor a ecting the electrical properties of the junction is the local geom etry of the molecule-electrode contact. It is generally accepted that, upon self-assem bly on gold, thicks lose the end hydrogens and then bind directly to the gold atom s. The preferential binding position of sulfur atom s on the Au (111) surface is at the apex of the pyram id with a triangular base of gold atom s (hollow position). A lso possible is the top position, where the sulfur is positioned directly above one of the gold atom s [12]. In this paper, we assume the hollow binding position of the sulfur. In the hollow position, the end S states strongly hybridize with states on gold atoms, and the resulting current is less dependent on exact molecule-contact geom etry in comparison to the top position [19]. Starting with the equilibrium molecular structure we remove the end hydrogens and replace them with two clusters

	" _s (eV)	"p (eV)	U (eV)	N um ber of electrons
С	-6.91	-17.52	8.7	4
Н	-7.85	{	11.5	1
S	-20.80	-6.47	7.8	6
Au	-5.88	{	6.7	1

TABLE I. Tight-binding parameters of atoms used in transport calculations.

of three gold atom s. The clusters form -bonds to sulfurs instead of the lost hydrogens. The prim ary molecule axis is roughly perpendicular to the planes of the gold triangles. The resulting molecular complexes (three gold atom s { dithiolate { three gold atom s) are organized in a periodic two-dimensional lm which is placed between two (111) surfaces of sem i-in nite gold electrodes. The lm is commensurate with the Au (111) surface but its primitive surface cell is four times larger.

In order to obtain the I-V characteristic of the device we use the Landauer form ulation of quantum transport [14] together with a sem i-em pirical tight-binding param – eterization of the H am iltonian m atrices for the m olecule and the electrodes. The o -diagonal m atrix elements of the m olecule are taken from H arrison [15]. They all are Slater-K oster linear combinations [16] of the four basic elements W

$$W \qquad (i \quad j) = 7:62 \frac{d_{ij}^2}{d_{ij}^2} eV; \qquad (6)$$

where d_{ij} is the distance between atoms i and j, and ss = 1:40, sp = 1:84 pp = 3:24, and pp =

0.81. The diagonalm atrix elements, that is on-site energies " $_i$ of core atom ic orbitals, are also adopted from [15], while the on-site energies of valence orbitals are calculated from atom ic a nities A $_i$ and ionization potentials I $_i$ as discussed in [19]

$$\mathbf{u}_{i} = \frac{\mathbf{I}_{i} + \mathbf{A}_{i}}{2} \mathbf{:}$$
(7)

The a nity and ionization potential determ ine the atom ic Hubbard parameter U_i as well:

$$U_{i} = I_{i} \qquad A_{i}: \qquad (8)$$

Table I lists the m olecular tight-binding param eters used in this paper.

O urparam eterization for the electrodes is based on the param eter sets of P apaconstantopoulos [17]. A lthough our calculational procedure enables us to treat the leads with the full set of s, p, and d orbitals [18,20], for the purposes of this paper the details of the electrode electronic structure are not im portant. We therefore choose to work with the s component of the band structure only. The W ss param eter of R ef. [17] for gold is 0:909 eV.

W e found, however, that this value results in too narrow a band with the high-energy edge being not very far from the conducting LUM O of MR. In order to separate m olecular recti cation from the specice ects associated with gaps in the leads' density of states, we also used the double value, $W_{ss} = 1.818 \text{ eV}$. The same value of W_{ss} is used for matrix elements inside the electrode and between the electrode surface and atom ic triangles that are part of the molecules. A comparison of the results obtained using the two values of W ss will be given in Section IV. The second important parameter is the Fermi energy of the electrodes (that is m inus the work function of the lead m aterial). The e ectiveness of our recti cation mechanism depends critically on $\mathrm{E}_{\,\mathrm{F}}$. Therefore we choose to study a series of E_F which in itates the e ect of using di erent electrodes. In particular, we studied the six values $E_F = 4.0, 4.2, 4.5, 5.0, 5.2, and$ 5:5 eV.

Calculation of current is perform ed utilizing a multistep procedure. First, an isolated molecular complex (three A u atom s { dithiolate { three A u atom s) is treated as follows. The molecular H am iltonian H m ol is constructed from the parameters described above. Then the molecular wave functions and their energies are found by diagonalizing the matrix E $\hat{H}_{m ol}$. From the wave functions, the average number of electrons on each atom is calculated:

$$q_{i} = 2 \qquad j_{n i} j_{i}^{2}; \qquad (9)$$

where the index n numbers the molecular orbitals and $_{\rm i}$ the atom ic orbitals that belong to atom i. A fler that the diagonalm atrix elements of H $_{\rm m\,ol}$ (the onsite energies "_i) are recalculated as

$$\mathbf{u}_{i}^{0} = \mathbf{u}_{i} + U_{i} (q_{i} \quad Z_{i}); \qquad (10)$$

where Z_i is the atom ic charge of the i-th atom, which in turn changes the charges q_i on the atom ic sites. Then the procedure is repeated until the charges q_i converge. The converged charges de ne the nal position of the m olecular levels and the m olecular H am iltonian to be used in the transport calculations.

In the second step, the sem i-in nite electrodes are solved. In our approach, there are two global quantum numbers, total energy E and momentum parallel to the surface k_k . Fixing k_k converts the sem i-in nite threedimensional problem into a sem i-in nite one-dimensional problem with a nite dimensional basis. Notice, how ever, that the H am iltonian of the one-dimensional wire explicitly depends on k_k . Thus transport problem s at dierent k_k are not equivalent. Moreover, the dependence on this quantum number could be substantial. It is important therefore to consider a grid of k_k and the grid should be as dense as possible. Then we follow the procedure of R ef. [20], modied for the presence of an arbitrary oriented surface. For each E and k_k , we solve the channel problem, i.e. nd all the B loch vectors with both real and complex k_z vectors. The former correspond to open conducting channels while the latter to evanescent channels. The wave functions and k_z values of the channels are used to construct the surface G reen's functions of the electrodes. Note that no energy or momentum integration is required with this method.

On the next step, the molecule is eliminated from the picture by rst solving the Schrödinger equation for the molecular wave function and then substituting the solution into the Schrödinger equation for the surface atoms of the leads. As a result of such a procedure, a matrix operator \hat{V} appears that directly couples states on the left wire with the states on the right wire. \hat{V} is essentially the inverse of E $\hat{H}_{m\ ol}$ convoluted with the matrices that describe the molecule electrode coupling. Therefore, it contains all the information about the molecule. In particular, \hat{V} has poles at the energies of the molecular orbitals. Knowing \hat{V} and the Green's functions of the free electrodes, the full electrode G reen's function is found from the D yson equation [20]

$$\hat{G} = (\hat{G}_0^{\ 1} \quad V)^{\ 1};$$
 (11)

where \hat{G}_0 is the block-diagonalm atrix in which the upper left corner is the free surface G reen's function of the left wire and the bottom right corner is that of the right wire. N ote that the size of all the matrices involved in Eq. (11) is equal to the combined dimension of the left and right electrode surfaces. In the present study, each surface unit cell has four states, therefore all the matrices are (8).

Since the Green's function solves Schrodinger's equation for non-coincident spatial arguments, the transm ission coecients t_{nn^0} (E; k_k) between the open channels can be found by multiplying \hat{G} by certain projector vectors \hat{P} . Each projection recovers an incident wave in one of the open channels in a particular electrode. The components of the vector $\hat{G}\hat{P}$ determ ine the transm ission and relectrodes [20]. The contribution to current is found by squaring the transm ission coecients and summing over the open channels of the receiving wire. The total current is obtained by summing over all the incident channels available, then over k_k , and integrating over energy E:

$$I(V) = \frac{2q}{h} \frac{X}{\sum_{E_F} + qV = 2} dET(E)$$
(12)

$$\Gamma(E) = \sum_{nn^{0}}^{X} t_{nn^{0}} (E; k_{k})^{2} :$$
(13)

In the present study, we have used a grid of 64 $k_{\rm k}$ points uniform ly distributed over the two dimensional surface B rillouin zone.

A n important and technically dicult problem is to account for the additional charge that the molecule acquires due to the m ism atch of its equilibrium chem ical potential with the Ferm i energy of the electrodes. All the m olecular components of the scattering wave functions could be found from the sam e G reen's function (11). Squaring them and integrating over energy, one nds new charges on the m olecule, much like Eq. (9). Then the new on-site m olecular energies are computed according to Eq. (10). Thus in principle, the entire calculational procedure described above (except the nal calculation of current) has to be repeated m any tim es until the charges converge. M oreover, this self-consistent procedure has to be perform ed anew for every value of the external bias voltage V, i.e. out of equilibrium. The charges in this non-equilibrium case can be calculated with the use of the procedure described in [19].

The additional charge transfer is most important for strong coupling between the molecule and the wires. In this case, the molecular levels broaden signi cantly so that their tails can accommodate signi cant additional charge. Luckily, our rectication mechanism works best for narrow molecular resonances. As long as the Ferm i energy remains below the conducting molecular level, the additional charge is negligible. For this reason, we do not perform the self-consistent calculation of charge in this paper. What we do take into account is the linear shift of the on-site atom ic energies due to the external electric eld due to the bias voltage.

IV . R E SU LT S

W e begin by presenting our num erical results for the electrode density of states N (E) (DOS), see Fig. 4. C learly visible are the square root singularities, which are characteristic of one-dim ensional conductors. Recall that xing kk renders the wire one-dimensional and the threedim ensionality is restored upon sum mation over the innite num ber of k_k points. The com parison of the main panel and inset in Fig. 4 indicates that this is indeed the case. Our choice of 64 k_k points is a reasonable com prom ise between the accuracy and time for the transport calculations. The DOS a ects the I-V characteristic of the diode in two ways. First, it changes the e ective resonance width since / N (E). Thus, in the case of 1:818 eV, the resonances are expected to be $W_{ss} =$ 0:909 eV (N / D ¹.) twice as narrow as for W $_{\rm ss}$ = Secondly, gaps/edges in the density of states could block elastic tunneling com pletely, resulting in a strong negative di erential resistance e ect. This possibility is discussed in Subsection (iv) below.

W e investigated four major e ects of the spatial and electronic structure of the junction on its I-V characteristic.

(i) E ect of the width of the molecular level on the recti cation property of the junction. W ithin our mechanism, good recti cation requires narrow molecular reso-



FIG.4. The bulk electrode density of states for the two values of W $_{ss}$. The data are collected from a (8 8) grid of k points, the one-dimensional square-root singularities being visible. The vertical solid line indicates the position of the Ferm i level. Inset: the same density of states but computed on a (40 40) grid of k points.

nances. If the levels are narrow, the current rises steeply upon reaching the threshold voltage. In other words, there is very little current before the resonance is reached but some nite current after, which can produce a high recti cation ratio. In the case of a broad resonance, the Lorentzian tails of the transmission function provide a sizeable current even before the nom inal threshold voltage is reached. The recti cation ratio should be sm all in this case. The width of the resonance is controlled by the thickness of the shorter insulating barrier. In Fig. 5 we compare the transmission function for the three molecular recti ers which have no, one, and two insulating -CH2-groups on the short side. One can see that in the rst two cases the resonance has a sizeable width of 0.2eV (full width at half maximum), which implies strong coupling to the electrode. This is more or less obvious for n = 0, when the sulfur atom is directly attached to the benzene. The lone electron pair of the sulfur overlaps with the electrons of the ring, resulting in a molecular orbital distributed alm ost evenly over the ring and the sulfur. Since the sulfur is directly coupled to the electrode (albeit through an interm ediate triangle), the molecular orbital is signicantly broadened. In the n = 1recti er, the sulfur is separated from the ring by a single insulating -CH2-group. How ever, because of the sp3 hybridization of carbon, the sulfur atom is out the plane of the ring. Then the separation between the sulfur and the ring is not large enough to prevent elongated p-orbitals of sulfur and carbon from direct overlapping. As a result,



FIG. 5. Transm ission probability through m olecular diodes Au_3 -S-(CH₂)_n-C₆H₄-(CH₂)₆-S-Au₃, n = 0;1;2. The peak corresponds to transm ission through the LUM O located on the benzene unit.

the electronic level is still signi cantly broadened. The situation changes radically for n = 2. Two insulating groups move the sulfur away from the ring by 4.3 A, so that direct overlap between the sulfur and the ring wave function becomes small. (From this point, insertion of new groups results in an exponential decrease of overlap.) A coording to our calculations, for n = 2 the width is just 10 m eV, see Fig. 5.

The num erical results illustrate the general form ula for transm ission probability T (E), Eq. (4). For the present molecular diodes, one partial level width is much larger than the other, say $_{\rm L}$ $_{\rm R}$. Then transmission at the resonance is T (E = E_{MO}) = 4 $_{R}$ = $_{L}$. Thus, as L decreases due to better insulation, the resonance gets narrow but higher. For the n = 2 diode, the resonance is narrow enough to be comparable with therm al, disorder, and other types of broadening present in the system . Further increase of the short barrier is unnecessary, it will result only in reducing the molecular asymmetry and spoiling the recti cation property. Our conclusion from this analysis is that two -CH2- groups on the short side is the optim al choice for recti cation. One should add that this rule has been derived for thicl-term inated molecules that are self-assembled on gold or other noble m etal. For other types of contact, this m ay change. For instance, when an LB lm is deposited on a metallic surface, a larger (Van-der-W aals-like) gap may exist between the lm and the metal. Such a gap will serve as an additional insulator, which may reduce the optimal length of insulating material on the molecule itself.

(ii) E ect of the metal work function on the forward



FIG. 6. The eect of the metal work function on the I-V characteristic of the molecular diode $-S-(CH_2)_2-C_6H_4-(CH_2)_6-S-$.

and reverse voltages. A coording to Eqs. (2) and (3), the forward and reverse voltages are directly proportional to the equilibrium energy di erence between the conducting m olecular leveland the Ferm ienergy of the m etal. W e have studied this e ect by varying the electrode Ferm ienergies with respect to the molecular orbitals. The results are presented in Fig. 6 and in Table II. The I-V characteristics all have sim ilar shape but their forward and reverse voltages system atically increase with , as expected. A nalysis of param eters from Table II reveals that $1:6, V_{R} =$ the ratios $V_F =$ 2:6, and $V_R = V_F$ 1:6 all rem ain approxim ately constant as functions of for m = 2 and n = 6. Thus the ratio $V_R = V_F$ is independent of electrode m aterial and is indeed a characteristic of the molecule asymmetry only. However, the relation $L_{right}=L_{left}$ is satis ed only approximately. $V_R = V_F =$ For the (2,6) m olecule, presented in Fig 6, $L_{right} = L_{left} = 3$ which is alm ost twice the voltage ratio. This is because the simple equations (2) and (3) do not take into account the voltage drop on the central conductive unit. Clearly, some voltage always drops there, which e ectively increases the lengths of both barriers and reduces the anisotropy. We discuss this issue in more detail in subsection (iii) below .

The last two columns of Table II present data on current recti cation. As a measure of the latter, we choose to compare currents at some positive and negative voltages with the same absolute value $V_{\rm op}$. O by by recti cation is strongest if $V_{\rm op}$ is chosen between $V_{\rm F}$ and $V_{\rm R}$. In this case, in the positive direction there is already some appreciable current due to resonant tunneling through the molecular level. In the reverse direction, the tunnel-

ing is still under barrier and therefore is exponentially reduced. This is the essence of our recti cation mechanism. The values of the operating voltage $V_{\rm op}\,$ shown in the table are roughly halfway between $V_{\rm F}\,$ and $V_{\rm R}$. (Approximately, $V_{\rm op}\,$ 1:3VF .) One can see that the current ratio is a steadily increasing function of . The overall dependence is close to linear, with both end points being slightly of this general trend.

An interesting problem is choosing an optim al value of . A swe have seen, large s result in better recti cation of current and wider recti cation voltage windows V_R VF. The latter fact is very important because all sorts of disorder in the system will tend to shrink the working window. A lso, a particular circuit design may require the operating reverse voltage must be larger in absolute value than a certain voltage. In general, the absolute value V_R has to be as large as possible. Both these arguments favor a large . On the other hand, large operating voltages in ply higher power and higher electrostatic stress on the molecules, which are, of course, undesirable. Quantitative understanding of this trade o problem warrants a detailed investigation for a particular application.

(iii) E ect of the length of the insulating barrier on the asymmetry of the I-V characteristic and on the overall current magnitude. This e ect is central to the present paper. By increasing the length of the borger barrier while keeping the shorter one xed, one forces a larger portion of the voltage to drop on the longer barrier. This implies that the conducting threshold is reached at di erent bias voltages in the two opposite directions, as illustrated in Fig. 2. This design principle provides us with them eans to system atically increase the current recti cation ratio and produce betterm olecular diodes. In Fig. 7, we show the calculated I-V characteristics of a series of molecular diodes (2;n) for work function W = 4:0 eV. The electrical parameters of the I-V characteristics are

W (eV)	(eV)	V _F (V)	V_R (V)	$V_R = V_F$	V _{op} (V)	I+ =I
4.0	0.55	0.90	1.44	1.60	1.13	56
4.2	0.75	1.19	1.93	1.62	1.41	118
4.5	1.05	1.66	2.73	1.64	2.07	173
5.0	1.55	2.51	4.01	1.60	3.02	276
52	1.75	2.77	4.50	1.63	3.68	305
5.5	2.05	3.25	5.32	1.64	4.25	323

TABLE II. Param eters of the I-V characteristics shown in Fig. 6 for m = 2 and n = 6. = W $f_{\rm L\,U\,M\,O}$ j is computed from the work function W and the molecular orbital energy $E_{\rm L\,U\,M\,O}$ = 3:45 eV. $V_{\rm F}$ and $V_{\rm R}$ are the current onset voltages under positive and negative bias, respectively. $V_{\rm op}$ is some operating voltage between $V_{\rm R}$ and $V_{\rm F}$. The last column represents typical current recti cation ratios $I_{\rm t}$ = I $(+V_{\rm op})$ =I ($V_{\rm op}$).



FIG.7. Dependence of the I-V characteristic on the asym – metry of the molecular diode HS-(CH₂)₂-C₆H₄-(CH₂)_n-SH for work function W = 4.0 eV.Notice how the V_F goes down while V_R goes up, system atically shifting the I-V curve to the left from the origin.

sum m arized in Table III. The series begins with the symmetric m olecule n = 2, which produces a symmetric I-V characteristic with $V_R = V_F = 1:19$ V.W ith increasing n, V_F m onotonically decreases but V_R increases, resulting in a systematic shift of the I-V characteristic with respect to the origin. By n = 10, the reverse-to-forward voltage ratio reaches $V_R = V_F = 2:18$. The voltage ratio grows slower than / n=2, suggested by Eqs. (2) and (3). It could be described by the relation

$$\frac{V_R}{V_F} = \frac{L_{right} + 4 L}{L_{left} + 4 L}; \qquad (14)$$

where 4 L is a correction that takes into account the voltage drop on the central conducting unit. Using the data of Table III, one nds 4 L=L left = 2:5, 4.0, 4.0, and 4.9 for n = 4, 6, 8, and 10, respectively. The correction does not remain constant as a function of n. Therefore it is di cult to assign to it a useful geom etricalm eaning.

The penultim ate column of Table III shows the current recti cation ratios $I_+ = I$. It grows approximately proportional to (n 2), reaching a value of 100 at n = 10.

The important issue is the exponential growth of the diode resistance with n, see the last colum n of Table III. This result is, of course, expected because the transm ission as wellas the current through them olecule is directly proportional to $_{\rm R}$, see Eqs. (4) and (5) at $_{\rm L}$ $_{\rm R}$. A sthe barrier length increases, the probability of underbarrier tunneling goes down exponentially fast, which is relected in the num erical data. A coording to our cal-

culations, addition of every extra pair of -(CH2)-groups increases the resistance by a factor of 17 2. Note that for (n = 2) ! (n = 4) the transition should not follow the same trend because at (n = 2) the molecule is symmetric and L = R.] Thus we have an unfavorable trade o problem where the recti cation ratio in proves linearly with n but the resistance and the time constant of the device worsens exponentially. This is an inherent feature of our mechanism and in some sense the price for its simplicity. W hen discussing the recti er resistances, one should not forget that what matters is the total resistance of an electronic element. W ith a typical target size of (10 10) nm², the num ber of m olecules per junction is going to be of order of 1000. Then even n = 8 and 10 diodes will have total resistances of 1-10 M , which amounts to a time constant 10¹⁰s for a 1 m long nanow ire, and 10⁶s for a 1 cm long nanow ire.

The data from Table II suggests that recti cation could be in proved further by increasing the initial energy difference . We computed IV characteristics for every value of the work function listed in Table II and for all MRs (m;n) with m = 1;2 and n = 2;4;6;8;10. [In addition, everything was calculated for the two values of the electrode matrix element W $_{\rm SS}$, bringing the total num – ber of studied I-V s to 120.] All the curves have shapes similar to those in Figs. 6 and 7, therefore we do not show them explicitly. Table IV sum marizes the results on recti cation ratios for a variety of combinations. A s expected, the recti cation ratio grows with both W and n. The maximum ratio of above 500 was observed for n = 10 and W = 5:2 eV (= 1:75 eV).

(iv) Role of energy gaps in the electrodes' density of states. Thise ect is not generic and potentially applies to sem iconductor electrodes only. Nevertheless, it o ers an interesting possibility to enhance the recti cation property of the diode by inhibiting current ow in the reverse direction due to an energy gap in the density of states. The basic idea is illustrated in Fig. 8. At some voltage V_g , the bottom of the gap aligns with the conducting m olecular orbital. At higher $V > V_g$ resonant tunneling becomes in possible due to the lack of available nalelectronic states. A coordingly, the current m ust drop to zero at $V = V_g$. If V_g lies in between V_F and V_R , then there

n	V _F (V)	V _R (V)	$V_R = V_F$	V _{op} (V)	$I_{+} = I$	r (M
2	1.19	1.19	1.00	any	1	0.33ª
4	0.99	1.28	1.29	1.13	32	2.40
6	0.90	1.44	1.60	1.13	56	42.6
8	0.81	1.61	1.99	1.13	76	836
10	0.80	1.74	2.18	1.13	104	13 , 150

TABLE III. Parameters of the I-V characteristics shown in Fig.7.R is the resistance of one molecule at V = + V_{op}.^a resistance at V = 1:6V.

W (eV)	4.0	4.2	4.5	5.0	5.2	5.5
(eV)	0.55	0.75	1.05	1.55	1.75	2.05
(1,2)	4 ^a	5 ^b	8 ^c	12 ^d	39	56
(1,4)	10 ^a	13 ^b	26 ^c	75	111	154
(1,6)	15	25	44	112	127	152
(1,8)	16	25	44	91	143 ^e	126
(1,10)	19	27	47	85		123
(2,4)	32	52	91	138	156	154
(2,6)	56	74	173	276	374	444
(2,8)	76	92	225	N/C	438 ^e	N/C
(2,10)	104	118	290	N/C	556°	N/C
V_{op} (V)	1.13	1.51	2.08	3.02	3.50	3.97

TABLE IV. The recti cation ratio $I_+ = I$ for six values of the wire work function and nine di erent m olecules. The rst colum n is the (m;n) numbers of the diodes. The top row is the work function of the electrodes in eV. The bottom row is the operating voltage V_{op} in volts, at which the recti cation ratio is reported. N/C " stands for non-conclusive evidence due to numerical noise in calculating sm all currents under reverse bias. Best recti cation is achieved for the (2,10) M R at W = 5.2 eV (in bold). The W value is close to the work function of gold.

^a at V = 1:32 V. ^b at V = 1:89 V. ^c at V = 2:46 V. ^d at V = 3:59 V. ^e at V = 3:02 V.

will be some substantial current in the forward direction in the interval $V_F < V < V_g$, Fig. 8(b), while no current at all in the reverse direction, Fig. 8(c). In the latter case, the gap of the right electrode is reached before the left Ferm i energy aligns with the conducting orbital.

The above argum ent does not take into account inelastic processes. If included, they would result in a non-zero current even in the situation of Fig. 8(c). In this case, the electrons can tunnel under the right barrier with irradiation of phonons, arriving at the right electrode with a reduced energy for which there are available states at the top of the valence band. In this paper we assume that the elastic tunneling is the dom inant transport mechanism and such processes can be neglected. W e have m odeled this e ect by using the sm aller electrode m atrix element $W_{ss} = 0.909 \text{ eV}$. Typical I-V characteristics are shown in Fig.9 and their param eters are sum m arized in Table V. W ith increasing W (and), the forward and reverse voltages V_F and V_R increase in accordance with Eqs. (2) and (3). At the same time, $V_{\rm q}$ decreases because the bottom of the energy gap m oves closer to the conducting m olecular level. As a result, the window of resonant tunneling is squeezed from both sides and at some critical W vanishes altogether. This e ect can be seen in Fig.9. In the reverse direction, the peak disappears between W = 42eV and W = 4.5 eV. In the forward direction, the same



FIG.8. (a) A gap in the density of states of the electrodes. (b) Under forward bias, when the right Ferm i level aligns with the LUMO, there are still states available in the left electrode. The current ows. (c) Under reverse bias, by the time the left Ferm i level aligns with the LUMO, there are no states available in the right electrode. The elastic current is blocked.

happens between W = 5:2 eV and W = 5:5 eV. (O f course, resonant tunneling survives longer in the forward direction because $V_F > V_R$.)

Notice that the I-V sofF ig.9 display large negative differential resistance under positive bias. In this respect, ourm olecular diodes behave sim ilarly to the conventional sem iconducting tunneling diodes. How ever, under negative bias, the behavior is quite di erent. W hile the tunneling diodes conduct very well under reverse bias, our M R conduct very little.

V.CONCLUSIONS

The major purpose of this paper has been to predict several trends in the I-V characteristics of MR when they are dominated by resonant tunneling through a certain molecular orbital localized on the conjugated part of a spatially asymmetric molecule. To achieve a large recti-



FIG.9. I-V characteristic of the (2,8) M R for the electrode m atrix element W _{ss} = 0:909 eV. A gap in the electrode's density of states cuts o current at large voltages. A part from current recti cation, this leads to a signi cant negative di erential resistance e ect. The latter will be reduced if inelastic processes are taken into account.

cation ratio, the conjugated part of the molecule must be connected to electrodes by insulating molecular groups of dierent length. By varying the ratio between the barrier lengths, one can achieve a rectication ratio of several hundred while keeping the current through the molecule at measurable levels.

As far as the described mechanism of molecular rectication is concerned, the observed trends could be divided into \spatial" and \energetic" domains. The spatial trends refer to the changes in the I-V characteristic that follow from changing the lengths of the two insulating barriers of the MR. The length of the shorter barrier controls the width the molecular resonance. We have

W (eV)	(eV)	V _F (V)	V _R (V)	Vg (V)	V_{op} (V)	$\mathbb{I}^+ = \mathbb{I}$
4.0	0.55	0.84	1.62	N/C	1.23	70
4.2	0.75	1.17	2.16	N/C	1.80	151
4.5	1.05	1.58	N/C	5.20	2.17	282
5.0	1.55	2.33	N/C	3.68	2.83	1308
5.2	1.75	2.60	N/C	3.10	2.83	1064
5.5	2.05	N/C	N/C	N/C	2.83	3

TABLE V. Param eters of the I-V characteristics of the (2,8) m olecular recti er for W $_{ss} = 0.909$ eV. (I-V s are shown in Fig. 9.) Notice how the recti cation ratio exceeds 1000 when the resonant conduction disappears in the reverse direction, but then drops to just 3 when it disappears in the forward direction too.



FIG.10. Other possible molecular diodes.

found the optim al length to be two $-(CH_2)$ -groups. One such group does not provide su cient insulation of the conducting unit from the metal. As a result, the resonance is too broad and current asymmetry is not pronounced. M ore than two $-(CH_2)$ -groups m ake the resonance narrower than tem perature and disorder induced widths, which is not useful. Increasing the length of the longer barrier in proves the current recti cation ratio but increases the total resistance of the molecular diode. These trends can be observed experim entally by studying severalm olecules with di erent lengths of the longer chain but identical otherwise. The energetic trends refer to the dependence of the recti cation property on the work function of the electrode material and on the electron a nity of the molecule. The two quantities de ne the parameter , which is the most important energy scale in the problem . In general, larger leads to better recti cation but at the sam e tim e to larger operating voltages. These trends can also be checked experim entally by measuring, for instance, the same molecule on gold and silver electrodes, or by m easuring the m olecules with di erent conducting units (say, benzene and naphthalene) on the same set of electrodes.

M ost of our results are rather insensitive to changing the end (\anchor") groups. The role of the latter is to provide better connection to the electrodes. Thus the end groups could be adjusted to the particular experimental setup without signi cantly altering the electrical properties of the device. They could even be absent altogether if the measurement technique does not require covalent bonding between the molecules and the electrodes. The com position of the insulating barriers may be changed too. For instance, instead of alkane chains one could use a com bination of the alkane segments and saturated cyclic hydrocarbons, see Fig. 10. An advantage of this design is that the molecules have more or less the same cross section along their entire length. Therefore the packing of the $\mbox{ Im } w$ ill be m uch better. O n the other hand, such M R could be harder to synthesize.

These conclusions are certainly limited to the particular set of approximations used in the present study. For instance, we have ignored inelastic processes, which should become progressively more important for larger molecules and at larger bias voltages. Inelastic scattering generally increases the current through the system, since the carrier has more nal states to tunnel into when it can lose energy by exciting a vibronic excitation. In the present resonant case, when V exceeds the threshold, either $V_{\rm F}~$ or $V_{\rm R}$, there will be some electrons with energy higher than the energy of the LUM O resonance. Such electrons can still tunnel through the junction e ectively by rst loosing their energy and then tunneling resonantly. Thus the overall current will continue to grow after the initial sharp increase, in contrast to the elastic-only case where the current stays approximately constant. Additionally, a nite tem perature should smoothen the sharp features of the I-V characteristic, thereby reducing the recti cation ratio. The inclusion of inelastic processes would probably reduce the estimated rectication ratio.

In conclusion, we have described a simple principle for m olecular rectication. It requires only one conducting m olecular level located asymmetrically with respect to the electrodes. Theoretical calculations have shown that current rectication ratios of several hundred are achievable with this mechanism. Higher ratios are likely to be accompanied by a signi cant reduction in conductance, which will make such diodes less practical. We have m ade several predictions of how the rectication properties should change between di erent molecules and different electrode materials (work functions). These trends are experimentally veri able on families of structurally similar molecules. Such trends are signatures of resonant tunneling through molecules and could serve as proof of experimental observation of the latter.

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